The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

fixing a flexible substrate ~~having thermal shrinkage~~ capable of being thermally shrunk to a holding frame;

heating the fixed flexible substrate at a temperature that the flexible substrate is thermal-shrunk, and

forming a conductive film on the flexible substrate by a sputtering method.

2. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

fixing an outer circumference of a flexible substrate ~~having thermal shrinkage~~ capable of being thermally shrunk to a frame-shaped holding frame;

heating the fixed flexible substrate at a temperature that the flexible substrate is thermal-shrunk, and

forming an amorphous semiconductor film on the flexible substrate by a plasma CVD method.

3. (Previously Presented) A method of manufacturing a semiconductor device according to claim 1, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

4. (Previously Presented) A method of manufacturing a semiconductor device according to claim 1, wherein the holding frame comprises a ceramics-metal complex.

5. (Previously Presented) A method of manufacturing a semiconductor device according to claim 2, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

6. (Previously Presented) A method of manufacturing a semiconductor device according to claim 2, wherein the holding frame comprises a ceramics-metal complex.

7. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

fixing a flexible substrate ~~having thermal shrinkage~~ capable of being thermally shrunk to a holding frame;

heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk; and

forming a predetermined pattern over the flexible substrate by screen printing.

8. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

fixing an outer circumference of a flexible substrate ~~having thermal shrinkage~~ capable of being thermally shrunk to a frame-shaped holding frame;

heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk, and

forming a predetermined pattern over the flexible substrate by laser processing.

9. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

fixing an outer circumference of a flexible substrate ~~having thermal shrinkage~~ capable of being thermally shrunk to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C;

heating the fixed flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

forming a conductive film on the flexible substrate by a sputtering method.

10. (Currently Amended) A method of manufacturing a semiconductor device, comprising the steps of:

fixing an outer circumference of a flexible substrate ~~having thermal shrinkage~~ capable of being thermally shrunk to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C;

heating the fixed flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

forming an amorphous semiconductor film on the flexible substrate by a plasma CVD method.

11. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a first step of fixing an outer circumference of a flexible ~~having thermal shrinkage~~ capable of being thermally shrunk to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C and then heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

a second step of forming a predetermined pattern over the flexible substrate by screen printing.

12. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

a first step of fixing an outer circumference of a flexible substrate ~~having thermal shrinkage~~ capable of being thermally shrunk to a frame-shaped holding frame having a smaller thermal expansion coefficient than 10 ppm/°C and then heating the flexible substrate at a temperature that the flexible substrate is thermal-shrunk by 0.2% or more; and

a second step of forming a predetermined pattern over the flexible substrate by laser processing.

13. (Previously Presented) A method of manufacturing a semiconductor device according to claim 11, wherein a position of the flexible substrate is aligned by an alignment means of the holding frame in the second step.

14. (Previously Presented) A method of manufacturing a semiconductor device according to claim 12, wherein a position of the flexible substrate is aligned by an alignment means of the holding frame in the second step.

15. (Previously Presented) A method of manufacturing a semiconductor device according to claim 7, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

16. (Previously Presented) A method of manufacturing a semiconductor device according to claim 7, wherein the holding frame comprises a ceramics-metal complex.

17. (Previously Presented) A method of manufacturing a semiconductor device according to claim 8, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

18. (Previously Presented) A method of manufacturing a semiconductor device according to claim 8, wherein the holding frame comprises a ceramics-metal complex.

19. (Previously Presented) A method of manufacturing a semiconductor device according to claim 9, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

20. (Previously Presented) A method of manufacturing a semiconductor device according to claim 9, wherein the holding frame comprises a ceramics-metal complex.

21. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

22. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the holding frame comprises a ceramics-metal complex.

23. (Previously Presented) A method of manufacturing a semiconductor device according to claim 11, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

24. (Previously Presented) A method of manufacturing a semiconductor device according to claim 11, wherein the holding frame comprises a ceramics-metal complex.

25. (Previously Presented) A method of manufacturing a semiconductor device according to claim 12, wherein the flexible substrate comprises one selected from polyethylene naphthalate, polyethylene terephthalate, polyether sulfone, and polyimide.

26. (Previously Presented) A method of manufacturing a semiconductor device according to claim 12, wherein the holding frame comprises a ceramics-metal complex.

27-30. (Cancelled)

31. (Previously Presented) A method of manufacturing a semiconductor device according to claim 9, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

32. (Previously Presented) A method of manufacturing a semiconductor device according to claim 10, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

33. (Previously Presented) A method of manufacturing a semiconductor device according to claim 11, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.

34. (Previously Presented) A method of manufacturing a semiconductor device according to claim 12, wherein the thermal expansion coefficient is 6.5 ppm/°C or smaller.